



PTO/SB/08a (08-03)

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STATEMENT BY APPLICANT

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of 2

## Complete if Known

Application Number	10/709,780
Filing Date	05/27/2004
First Named Inventor	Davis Andrew McClure et al.
Art Unit	2811
Examiner Name	

Attorney Docket Number 5000.238A

## U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> ( <i>If known</i> )			
TT	1	US- 6,187,606 B1	02-13-2001	Edmond et al.	
TT	2	US- 6,120,600	09-19-2000	Edmond et al.	
TT	3	US- 5,523,589	06-04-1996	Edmond et al.	
TT	4	US- 5,900,647 A	05-04-1999	Inoguchi	
TT	5	US- 6,552,376 B1	04-22-2003	Koike et al.	
TT	6	US- 6,555,452 B2	04-29-2003	Nikolaev et al.	
TT	7	US- 6,632,694 B2	10-14-2003	Torvik	
TT	8	US- 3,629,011	12-21-1971	Tohi et al.	
TT	9	US- 2003/0006417 A1	01-09-2003	Klosowiak et al.	
TT	10	US- 2002/0031851 A1	03-14-2002	Linthicum et al.	
TT	11	US- 5,786,606 A	07-28-1998	Nishio et al.	
TT	12	US- 6,667,495 B2	12-23-2003	Friedrichs et al.	
TT	13	US- 5,273,933 A	12-28-1993	Halano et al.	
TT	14	US- 6,232,244 B1	05-15-2001	Ibok	
TT	15	US- 6,277,707 B1	08-21-2001	Lee et al.	
		US-			
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## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> ( <i>If known</i> )				
TT	16	PCT WO 00/79570 A2	12-28-2000	Advanced Tech. Materials		
TT	17	DE 199 44 144 A1	04-12-2001	Rossendorf Forschzent		✓

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04-06-2005

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<i>Art Unit</i>	2811
<i>Examiner Name</i>	

Attorney Docket Number 5000.238A

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
TT	18	F.J. CAMPOS ET AL.; Confocal Micro-Raman Characterization of Lattice Damage In High Energy Aluminum Implanted 6H-SiC; Journal of Applied Physics; January 1, 1999; pgs. 99-104; Vol. 85, No. 1; American Institute of Physics, New York, US	
TT	19	M.B. SCOTT ET AL.; High temperature (600 degrees C) implantation study of P+ and N+ implanted epitaxial N-type 4H-SiC; Compound Semiconductors 1998, Proceedings of the 25th International Symposium on Compound Semiconductors; Nara, Japan, October 12-16, 1998; pages 763-768; Vol. NR. 162; Institute of Physics Conference Series, London	
TT	20	ISSEY OHTA ET AL.; An Ideal-Profile Implantation Process for GaAs Analog MMICs; Proceedings of the Gallium Arsenide Integrated Circuit Symposium, Grenoble, Florida, October 28-30, 1986; pgs. 55-58; Vol. SYMP. 8; IEEE, New York, US	
TT	21	W.M. DUNCAN ET AL.; A Single Step Selective Implantation Technology for Multiply Doped Layers Using Proximity Annealing; IEEE Electron Device Letters; December 1981; pgs. 309-311; Vol. EDL-2, No. 12; IEEE Inc., New York, US	
TT	22	H. J. HOVEL; Implant Profile Adjustment with GaAlAs Caps; IBM Technical Disclosure Bulletin; February 1985; pgs. 5360-5361; Vol. 27, No. 9; IBM Corp., New York, US	
TT	23	S. K. LEE ET AL.; Electrical characterization of TiC ohmic contacts to aluminum ion implanted 4H-silicon carbide; Applied Physics Letters; Sept. 4, 2000; pp 1478-1480; Vol. 77, No. 10	

Examiner Signature

*Thien MMC*

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